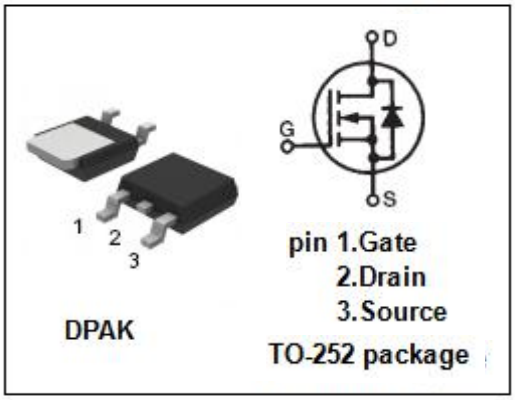
isc N-Channel MOSFET Transistor STD7ANM60N

- **FEATURES**
- With TO-252(DPAK) packaging
- High speed switching
- Low gate input resistance
- Standard level gate drive
- Easy to use
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



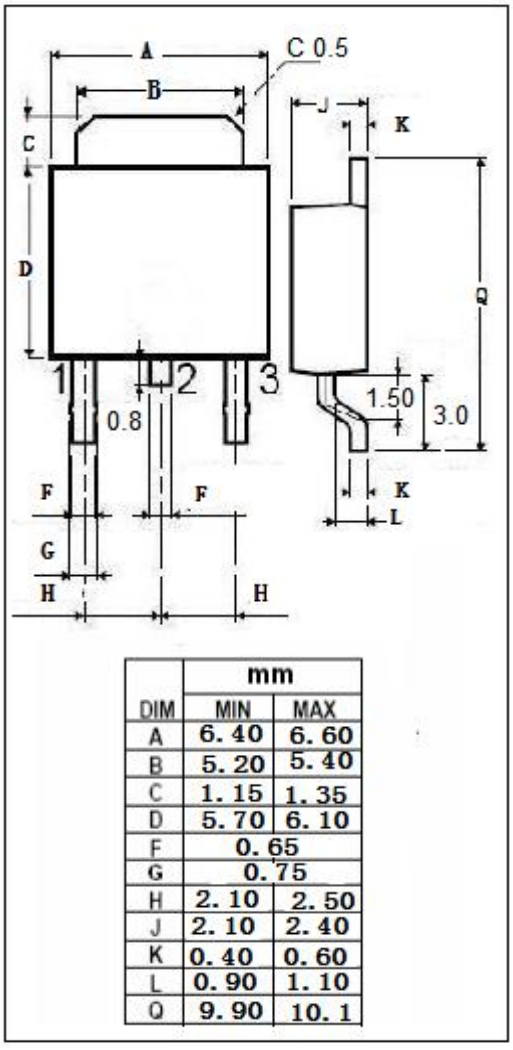
- **APPLICATIONS**
- Power supply
- Switching applications

- **ABSOLUTE MAXIMUM RATINGS(T_a=25℃)**

SYMBOL	PARAMETER	VALUE	UNIT
V_{DSS}	Drain-Source Voltage	600	V
V_{GSS}	Gate-Source Voltage	±25	V
I_D	Drain Current-Continuous;@Tc=25℃	5	A
I_{DM}	Drain Current-Single Pulsed	20	A
P_D	Total Dissipation	45	W
T_j	Operating Junction Temperature	150	℃
T_{stg}	Storage Temperature	-55~150	℃

- **THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
Rth(ch-c)	Channel-to-case thermal resistance	2.78	℃/W



DIM	mm MIN	MAX
A	6.40	6.60
B	5.20	5.40
C	1.15	1.35
D	5.70	6.10
F	0.65	
G	0.75	
H	2.10	2.50
J	2.10	2.40
K	0.40	0.60
L	0.90	1.10
Q	9.90	10.1

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V; I_D= 1mA	600			V
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}; I_D=0.25mA	2		4	V
$R_{DS(on)}$	Drain-Source On-Resistance	V_{GS}= 10V; I_D= 2.5A			900	mΩ
I_{GSS}	Gate-Source Leakage Current	V_{GS}=±20V;V_{DS}= 0V			±0.1	μA
I_{DSS}	Drain-Source Leakage Current	V_{DS}= 600V; V_{GS}= 0V			1	μA
V_{SDF}	Diode forward voltage	I_{SD}= 5A, V_{GS} = 0 V			1.3	V